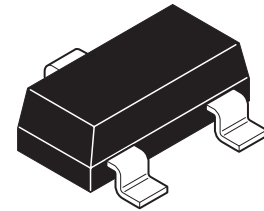


# ZXTP2039F

## SOT23 80 volt PNP silicon planar medium power transistor

### Summary

$V_{(BR)CEV} > -80V$   
 $V_{(BR)CEO} > -60V$   
 $I_{c(cont)} = -1A$   
 $V_{ce(sat)} < -600mV @ -1A$



### Complementary type

ZXTN2038F

### Description

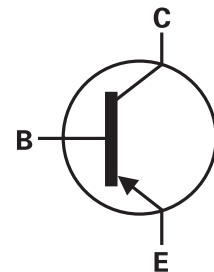
This transistor combines high gain, high current operation and low saturation voltage making it ideal for power MOSFET gate driving and low loss power switching.

### Features

- Low saturation voltage for reduced power dissipation
- 1 to 2 amp high current capability
- Pb-free
- SOT23 package

### Applications

- Power MOSFET gate driving
- Low loss power switching



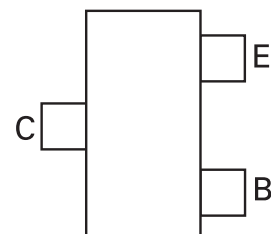
### Ordering information

Device	Reel size	Tape width	Quantity per reel
ZXTP2039FTA	7"	8mm	3,000
ZXTP2039FTC	13"	8mm	10,000

### Device marking

P39

Pin out - top view



# ZXTP2039F

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	$V_{CBO}$	-80	V
Collector-emitter voltage	$V_{CEV}$	-80	V
Collector-emitter voltage	$V_{CEO}$	-60	V
Emitter-base voltage	$V_{EBO}$	-5.0	V
Peak pulse current	$I_{CM}$	-2	A
Continuous collector current *	$I_C$	-1	A
Peak base current	$I_{BM}$	-1	A
Power dissipation @ $T_A=25^{\circ}C$ *	$P_D$	350	mW
Operating and storage temperature	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

### NOTES:

\* For a device surface mounted on a 15mm x 15mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

# ZXTP2039F

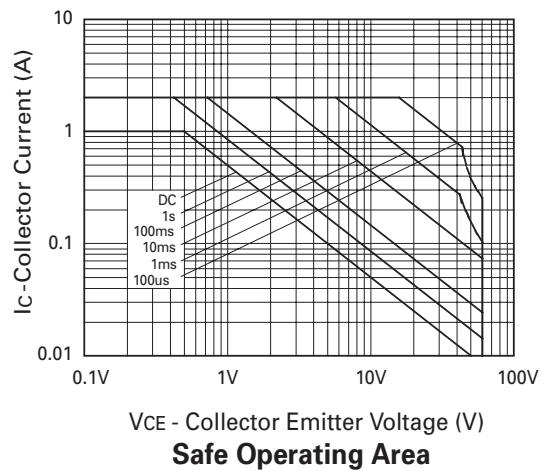
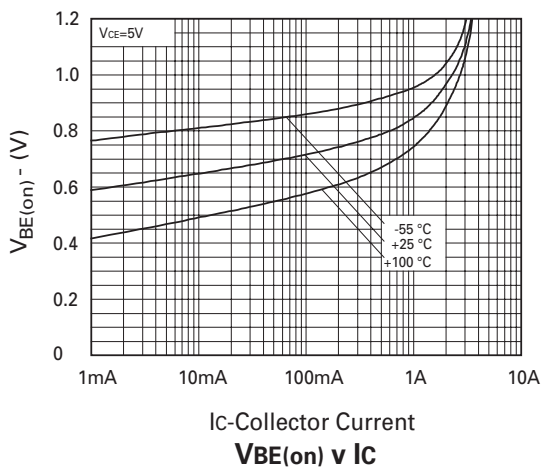
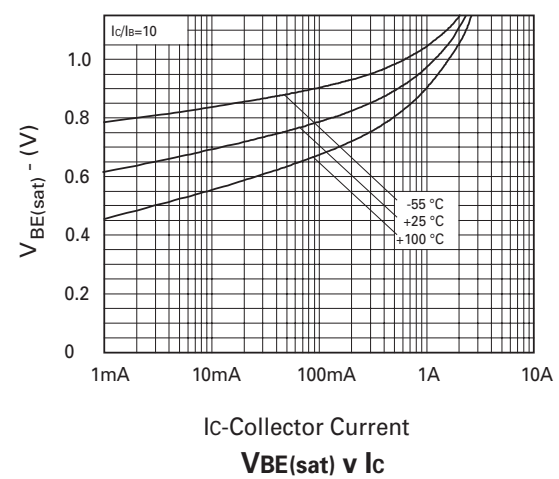
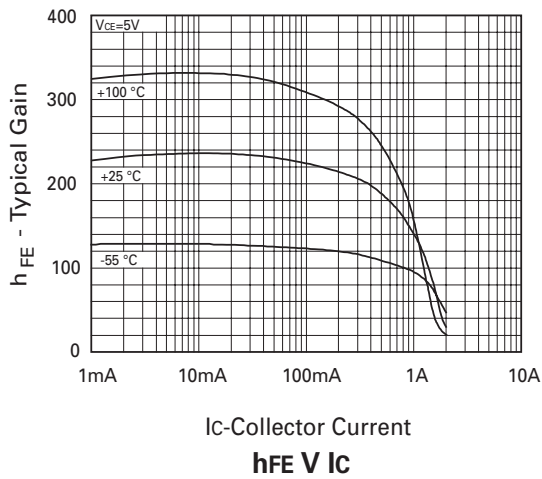
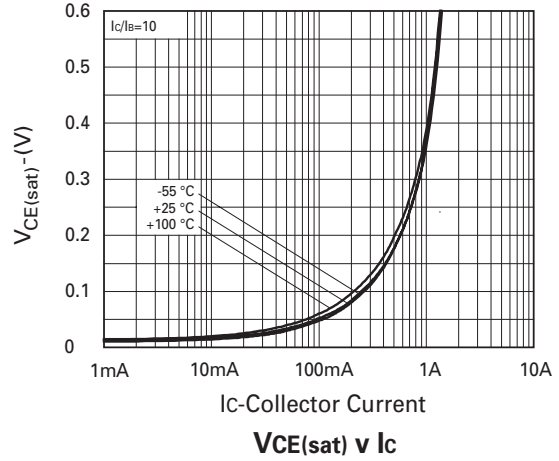
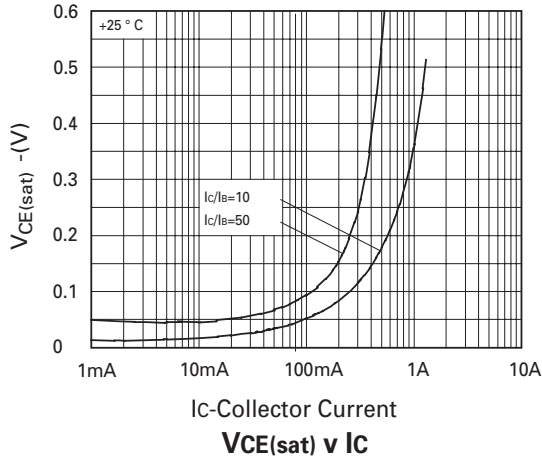
## Electrical characteristics (@T<sub>AMB</sub> = 25°C)

Parameter	Symbol	Min.	Max.	Unit	Conditions
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	-80		V	I <sub>C</sub> = -100μA
Collector-emitter breakdown voltage	V <sub>(BR)CEV</sub>	-80		V	I <sub>C</sub> = -1μA -0.3V < V <sub>BE</sub> < 1V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	-60		V	I <sub>C</sub> = -10mA *
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	-5		V	I <sub>E</sub> = -100μA
Collector-emitter cut-off current	I <sub>CES</sub>		-100	nA	V <sub>CE</sub> = -60V
Collector-base cut-off current	I <sub>CBO</sub>		-100	nA	V <sub>CB</sub> = -60V
Emitter-base cut-off current	I <sub>EBO</sub>		-100	nA	V <sub>EB</sub> = -4V
Static forward current transfer ratio	h <sub>FE</sub>	100 100 80 15	300		I <sub>C</sub> = -1mA, V <sub>CE</sub> = -5V I <sub>C</sub> = -500mA, V <sub>CE</sub> = -5V* I <sub>C</sub> = -1A, V <sub>CE</sub> = -5V* I <sub>C</sub> = -2A, V <sub>CE</sub> = -5V*
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>		-0.2 -0.3 -0.6	V V V	I <sub>C</sub> = -100mA, I <sub>B</sub> = -2mA* I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA* I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA*
Base-emitter saturation voltage	V <sub>BE(sat)</sub>		-1.2	V	I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA*
Base-emitter turn-on voltage	V <sub>BE(on)</sub>		-1.0	V	I <sub>C</sub> = -1A, V <sub>CE</sub> = -5V*
Transition frequency	f <sub>T</sub>	150			I <sub>C</sub> = -50mA, V <sub>CE</sub> = -10V f = 100MHz
Output capacitance	C <sub>obo</sub>		10	pF	V <sub>CB</sub> = -10V, f = 1MHz

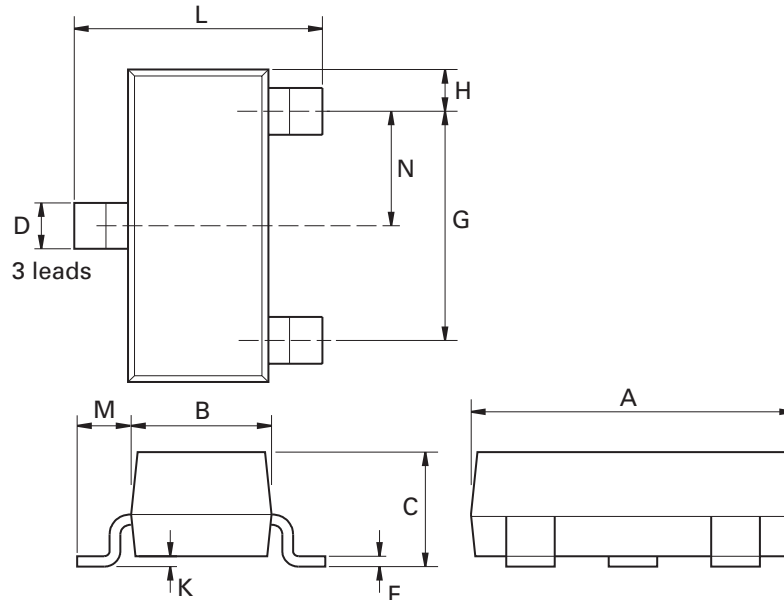
### NOTES:

\* Measured under pulsed conditions. Pulse width = 300μS. Duty cycle ≤ 2%  
Spice parameter data is available upon request for this device

## Typical characteristics



## Packaging details - SOT23



## Package dimensions

Dimensions in inches are control dimensions, dimensions in millimeters are approximate.

Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 Nom.		0.0375 Nom.	
G	1.90 Nom.		0.075 Nom.		-	-	-	-	-

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